

# Refine Search

10/630,969

## Search Results -

Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio)	1

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L6

Refine Search

Recall Text

Clear

Interrupt

## Search History

 DATE: Tuesday, June 29, 2004   [Printable Copy](#)   [Create Case](#)

<u>Set</u> <u>Name</u>	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L6</u>	L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio)	1	<u>L6</u>
<u>L5</u>	L3 and oxidation	20	<u>L5</u>
<u>L4</u>	L3 and oxidation and (sio2)	0	<u>L4</u>
<u>L3</u>	L2 and (inert or argon or ar or heliumn or he or neon or ne or kr or krypton or xenon or nitrogen)	45	<u>L3</u>
<u>L2</u>	L1 and ((ratio) near3 (nitrogen and oxygen))	45	<u>L2</u>
<u>L1</u>	microstructure	23090	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 1 of 1 returned.

☐ 1. Document ID: US 6071601 A

L6: Entry 1 of 1

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	RMC	Draw D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio)	1

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## Refine Search

### Search Results -

Terms	Documents
L5 and pressure and torr	5

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L7





### Search History

 DATE: Tuesday, June 29, 2004    [Printable Copy](#)    [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L7</u>	L5 and pressure and torr	5	<u>L7</u>
<u>L6</u>	L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1	<u>L6</u>
<u>L5</u>	L3 and oxidation	20	<u>L5</u>
<u>L4</u>	L3 and oxidation and (sio2)	0	<u>L4</u>
<u>L3</u>	L2 and (inert or argon or ar or heliumn or he or neon or ne or kr or krypton or xenon or nitrogen)	45	<u>L3</u>
<u>L2</u>	L1 and ((ratio) near3 (nitrogen and oxygen))	45	<u>L2</u>
<u>L1</u>	microstructure	23090	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

### Search Results - Record(s) 1 through 5 of 5 returned.

☐ 1. Document ID: US 6498097 B1

L7: Entry 1 of 5

File: USPT

Dec 24, 2002

US-PAT-NO: 6498097

DOCUMENT-IDENTIFIER: US 6498097 B1

TITLE: Apparatus and method of forming preferred orientation-controlled platinum film using oxygen

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw De
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☐ 2. Document ID: US 6071601 A

L7: Entry 2 of 5

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw De
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☐ 3. Document ID: US 6054331 A

L7: Entry 3 of 5

File: USPT

Apr 25, 2000

US-PAT-NO: 6054331

DOCUMENT-IDENTIFIER: US 6054331 A

TITLE: Apparatus and methods of depositing a platinum film with anti-oxidizing function over a substrate

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw De
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☐ 4. Document ID: US 5143879 A

L7: Entry 4 of 5

File: USPT

Sep 1, 1992

US-PAT-NO: 5143879

DOCUMENT-IDENTIFIER: US 5143879 A

**\*\* See image for Certificate of Correction \*\***

TITLE: Method to recover organic templates from freshly synthesized molecular sieves

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw	Doc
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☐ 5. Document ID: US 4762728 A

L7: Entry 5 of 5

File: USPT

Aug 9, 1988

US-PAT-NO: 4762728

DOCUMENT-IDENTIFIER: US 4762728 A

TITLE: Low temperature plasma nitridation process and applications of nitride films formed thereby

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw	Doc
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Clear

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Fwd Refs

Bkwd Refs

Generate OACS

Terms

Documents

L5 and pressure and torr

5

Display Format: TI

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# Hit List

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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
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## Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6548343 B1

L24: Entry 1 of 4

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6485988 B2

L24: Entry 2 of 4

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 6413386 B1

L24: Entry 3 of 4

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 6362093 B1

L24: Entry 4 of 4

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. D.
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L23 and (silicon adj oxynitride)	4

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## Refine Search

### Search Results -

Terms	Documents
L23 and (silicon adj oxynitride)	4

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L24

Refine Search

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### Search History

 DATE: Tuesday, June 29, 2004    [Printable Copy](#)    [Create Case](#)

<u>Set Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L24</u>	L23 and (silicon adj oxynitride)	4	<u>L24</u>
<u>L23</u>	L22 and (silicon adj oxide)	7	<u>L23</u>
<u>L22</u>	L21 and oxide and (oxygen adj containing)	11	<u>L22</u>
<u>L21</u>	L20 and semiconductor and (flow adj rate)	80	<u>L21</u>
<u>L20</u>	L19 and (inert or h2 or ne or ar or xe or neon or argon or krypton or kr)	1159	<u>L20</u>
<u>L19</u>	(hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	2645	<u>L19</u>
<u>L18</u>	L2 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L18</u>
<u>L17</u>	L11 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L17</u>
<u>L16</u>	L15 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L16</u>
<u>L15</u>	L11 and (inert or argon or neon or hydrogen or xenon or krypton)	56	<u>L15</u>
<u>L14</u>	L11 and (inert or argon or neon or hydrogen or xenon or krypton) and (high adj K)	0	<u>L14</u>
<u>L13</u>	L11 near10 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L13</u>



<u>L12</u>	L11 near5 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L12</u>
<u>L11</u>	(flow adj rate) near4 (3:1)	76	<u>L11</u>
<u>L10</u>	l2 and (3:1)	8	<u>L10</u>
<u>L9</u>	l2 and (nitrogen:oxygen)	0	<u>L9</u>
<u>L8</u>	n2:o2	2	<u>L8</u>
<u>L7</u>	L4 and (high adj K) and oxidation and chamber	3	<u>L7</u>
<u>L6</u>	L5 and (silicon adj oxide)	9	<u>L6</u>
<u>L5</u>	L4 and (oxygen adj containing)	19	<u>L5</u>
<u>L4</u>	L2 and nitrogen and oxygen and (inert or hydrogen or argon or h2 or ar or xenon or xe or krypton or kr or neon or ne)	88	<u>L4</u>
<u>L3</u>	L2 and ((nitrogen and oxygen) near2 (ratio))	3	<u>L3</u>
<u>L2</u>	(semiconductor or wafer) and (micro) and (flow near ratio)	231	<u>L2</u>
<u>L1</u>	microstructure near5 (flow ratio)	2	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 7 of 7 returned.

☐ 1. Document ID: US 6620670 B2

L23: Entry 1 of 7

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of AL2O3

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6583463 B1

L23: Entry 2 of 7

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized TA2O5 capacitor insulator

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 6548343 B1

L23: Entry 3 of 7

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 6544875 B1

L23: Entry 4 of 7

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWAC	Draw De
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☐ 5. Document ID: US 6485988 B2

L23: Entry 5 of 7

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWAC	Draw De
------	-------	----------	-------	--------	----------------	------	-----------	--	--	--------	------	---------

☐ 6. Document ID: US 6413386 B1

L23: Entry 6 of 7

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWAC	Draw De
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☐ 7. Document ID: US 6362093 B1

L23: Entry 7 of 7

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWAC	Draw De
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Clear

Generate Collection

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Fwd Refs

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Terms

Documents

L22 and (silicon adj oxide)

7

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Search Results - Record(s) 1 through 10 of 11 returned.

☐ 1. Document ID: US 6659111 B1

L22: Entry 1 of 11

File: USPT

Dec 9, 2003

US-PAT-NO: 6659111

DOCUMENT-IDENTIFIER: US 6659111 B1

TITLE: Cleaning gas and method for cleaning vacuum treatment apparatus by flowing the cleaning gas

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6620670 B2

L22: Entry 2 of 11

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of AL2O3

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 6583463 B1

L22: Entry 3 of 11

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized TA2O5 capacitor insulator

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 6548343 B1

L22: Entry 4 of 11

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 5. Document ID: US 6544875 B1

L22: Entry 5 of 11

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 6. Document ID: US 6509511 B1

L22: Entry 6 of 11

File: USPT

Jan 21, 2003

US-PAT-NO: 6509511

DOCUMENT-IDENTIFIER: US 6509511 B1

TITLE: Process for the conversion of perfluoroalkanes, a catalyst for use therein and a method for its preparation

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 7. Document ID: US 6485988 B2

L22: Entry 7 of 11

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 8. Document ID: US 6413386 B1

L22: Entry 8 of 11

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 9. Document ID: US 6362093 B1

L22: Entry 9 of 11

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 10. Document ID: US 6238582 B1

L22: Entry 10 of 11

File: USPT

May 29, 2001

US-PAT-NO: 6238582

DOCUMENT-IDENTIFIER: US 6238582 B1

TITLE: Reactive ion beam etching method and a thin film head fabricated using the method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L21 and oxide and (oxygen adj containing)	11

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## Hit List

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Search Results - Record(s) 11 through 11 of 11 returned.

☐ 11. Document ID: US 6218300 B1

L22: Entry 11 of 11

File: USPT

Apr 17, 2001

US-PAT-NO: 6218300

DOCUMENT-IDENTIFIER: US 6218300 B1

TITLE: Method and apparatus for forming a titanium doped tantalum pentaoxide dielectric layer using CVD

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L21 and oxide and (oxygen adj containing)	11

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### Search Results - Record(s) 1 through 3 of 3 returned.

☐ 1. Document ID: US 6387819 B1

L3: Entry 1 of 3

File: USPT

May 14, 2002

US-PAT-NO: 6387819

DOCUMENT-IDENTIFIER: US 6387819 B1

TITLE: Method for etching low K dielectric layers

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 2. Document ID: US 6110609 A

L3: Entry 2 of 3

File: USPT

Aug 29, 2000

US-PAT-NO: 6110609

DOCUMENT-IDENTIFIER: US 6110609 A

TITLE: Magnetic thin film and magnetic head using the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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☐ 3. Document ID: US 4543707 A

L3: Entry 3 of 3

File: USPT

Oct 1, 1985

US-PAT-NO: 4543707

DOCUMENT-IDENTIFIER: US 4543707 A

TITLE: Method of forming through holes by differential etching of stacked silicon oxynitride layers

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw Dc
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Terms	Documents
L2 and ((nitrogen and oxygen) near2 (ratio))	3

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